



<b>Form 1449 (Modified)</b>  <b>Information Disclosure Statement By Applicant</b>  (Use Several Sheets if Necessary)	<b>Atty Docket No.</b>	NOVLP097/NVLS-2906
	<b>Application No.:</b>	10/807,680
	<b>Applicant</b>	Wu et al.
	<b>Filing Date</b>	March 23, 2004
	<b>Group</b>	1792
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#### U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
	1.	7,208,389 B1	04.24.07	Tipton et al.			
	2.	7,253,125 B1	08.07.07	Bandyopadhyay et al.			
	3.	7,265,061	09.04.07	Cho et al.			
	4.	7,018,918	03.2006	Kloster et al.			
	5.	2006/0024976	02.2006	Waldfried et al.			
	6.	2007/0281497	12.2007	Liu et al.			
	7.	6,136,680	10.2000	Lai et al.			
	8.	2005/0156285 A1	07.2005	Gates et al.			
	9.	7,064,088 B2	06.2006	Hyodo et al.			
	10.	7,241,704 B1	07.10.07	Wu et al.			
	11.	7,176,144	02.13.07	Wang et al.			

#### Foreign Patent or Published Foreign Patent Application

Examiner Initial		Document No.	Publication Date	Country or Patent Office	Class	Sub-Class	Translation	
							Yes	No
	12.	01-107519	25.04.1989	Japan			X	

#### Other Documents

Examiner Initial	No.	Author, Title, Place (e.g. Journal) of Publication, Date
	13.	Schravendijk, et al., "UV Treatment of STI Films for Stress," Novellus Systems, Inc., Application No. 11/811,048, filed June 7, 2007. [NOVLP192/NVLS-3219]
	14.	Arghavani et al., <i>Strain Engineering in Non-Volatile Memories</i> , <u>Reed Business Information</u> , 2007, six pages.
	15.	Notice of Allowance and Fee Due mailed May 22, 2006, from U.S Application No. 10/672,311 [Atty Dkt No. NOVLP075/NVLS-2820].
	16.	Allowed Claims from U.S Application No. 10/672,311 [Atty Dkt No. NOVLP075/NVLS-2820].
	17.	Notice of Allowance and Fee Due mailed April 4, 2007, from U.S Application No. 10/825,888 [Atty Dkt No. NOVLP088/NVLS-2882].
	18.	Allowed Claims from U.S Application No. 10/825,888 [Atty Dkt No. NOVLP088/NVLS-2882]

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	19.	Bandyopadhyay et al., "Method to Improve Mechanical Strength of Low-K Dielectric Film Using Modulated UV Exposure," Novellus Systems, Inc., Application No. 11/824,049, filed June 28, 2007 [NOVLP088C1/NVLS-2882C1]
	20.	Notice of Allowance and Fee Due mailed October 10, 2006, from U.S. Application No. 10/800,377 [Atty Dkt No. NOVLP089/NVLS-2886/2887].
	21.	Allowed Claims from U.S. Application No. 10/800,377 [Atty Dkt No. NOVLP089/NVLS-2886/2887]
	22.	Allowed Claims from U.S. Application No. 10/860,340 [Atty Dkt No. NOVLP099/NVLS-2896]
	23.	U.S. Office Action mailed December 12, 2007, from U.S. Application No. 11/146,456 [Atty Dkt No. NOVLP100X1/NVLS-3040].
	24.	U.S. Office Action mailed October 3, 2007, from U.S. Application No. 11/115,576 [Atty Dkt No. NOVLP127/NVLS-3044].
	25.	Shaviv et al., "UV Treatment to Improve Integrity and Performance of Front End Dielectrics," Novellus Systems, Inc., Application No. 11/622,409, filed January 11, 2007. [NOVLP188/NVLS-3213]
	26.	van Schravendijk et al., "UV Treatment for Carbon-Containing Low-K Dielectric Repair in Semiconductor Processing," Novellus Systems, Inc., Application No. 11/590,661, filed October 30, 2006. [NOVLP190/NVLS-3216]
	27.	Shrinivassan et al., "Multi-Station Sequential Curing of Dielectric Films," Novellus Systems, Inc., Application No. 11/688,695, filed March 20, 2007. [NOVLP197/NVLS-3262]
	28.	Varadarajan et al., "A Cascaded Cure Approach to Fabricate Highly Tensile Silicon Nitride Films," Novellus Systems, Inc., Application No. 11/897,838, filed August 31, 2007. [NOVLP236/NVLS-3332]
	29.	Van den Hoek, et al., "VLSI Fabrication Processes for Introducing Pores Into Dielectric Materials," Novellus Systems, Inc., Application No. 11/606,340, filed November 28, 2006. [NOVLP100C1/NVLS-2956C1]
	30.	U.S. Office Action mailed January 10, 2008, from U.S. Application No. 11/622,423 [Atty Dkt No. NOVLP189/NVLS-3215].
	31.	Bhadri Varadarajan et al., "Development of High Stress SiN Films for Use with Strained Silicon Technologies"; Proc. 68 <sup>th</sup> Symp. On Semiconductors and IC Tech.; Kyoto 2005.
	32.	U.S. Notice of Allowance and Fee Due mailed September 19, 2007, from U.S. Application No. 10/800,409. [NOVLP098/NVLS-2907]
	33.	Allowed Claims from U.S. Application No. 10/800,409. [NOVLP098/NVLS-2907]
	34.	U.S. Office Action mailed October 4, 2007, from U.S. Application No. 10/820,525 [Atty Dkt No. NOVLP091/NVLS-2889].
	35.	Wu et al., "Methods For Producing Low Stress Porous Low-K Dielectric Materials Using Precursors With Organic Functional Groups", U.S. Application No. 11/764,750, filed June 18, 2007 [Atty Dkt: NOVLP106D1/NVLS-2930D1]

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	36.	U.S. Office Action mailed October 29, 2007, from U.S. Application No. 11/764,750 [Atty Dkt No. NOVLP106D1/NVLS-2930D1].
	37.	Wu et al., "Methods For Producing Low-K CDO Films," U.S. Application No. 11/936,754, filed November 7, 2007 [Atty Docket No.: NOVLP098D1/NVLS-2907D1]
	38.	Wu et al., "Methods For Improving Integration Performance of Low Stress CDO Films", U.S. Application No. 11/936,752, filed November 7, 2007 [Atty Dkt: NOVLP107D1/NVLS-2932D1]
	39.	U.S. Notice of Allowance and Fee Due mailed September 27, 2007, from U.S. Application No. 11/376,510. [NOVLP099D1/NVLS-2896D1]
	40.	Allowed Claims from U.S. Application No. 11/376,510. [NOVLP099D1/NVLS-2896D1]
	41.	U.S. Office Action mailed July 12, 2006, from U.S. Application No. 10/672,305 [Atty Dkt No. NOVLP069/NVLS-2821].
	42.	U.S. Office Action mailed August 14, 2007, from U.S. Application No. 10/404,693 [Atty Dkt No. NOVLP064/NVLS-2794].
	43.	U.S. Office Action mailed February 2, 2007, from U.S. Application No. 10/672,305 [Atty Dkt No. NOVLP069/NVLS-000821].
	44.	Willibrordus Gerardus Maria van den Hoek et al., "VLSI Fabrication Processes for Introducing Pores Into Dielectric Materials," U.S. Application No. 11/606,340, filed November 28, 2006 (Atty Dkt: NOVLP100C1/NVLS-2956C1)
	45.	Cabarrocas et al., "Plasma production of nanocrystalline silicon particles and polymorphous silicon thin films for large-area electronic devices," Pure Appl. Chem., Vol. 74, No. 3, pp. 359-367, 2002.
	46.	Kim et al., "Particle formation during low-pressure chemical vapor deposition from silane and oxygen: Measurement, modeling, and film properties," J. Vac. Sci. Technol. A 20(2), Mar/Apr 2002, pp. 413-423.
	47.	Suh et al., "Modeling particle formation during low-pressure silane oxidation: Detailed chemical kinetics and aerosol dynamics," J. Vac. Sci. Technol. A 19(3), May/Jun 2001, pp. 940-951.
	48.	Ostraat, et al., "Ultraclean Two-Stage Aerosol Reactor for Production of Oxide-Passivated Silicon Nanoparticles for Novel Memory Devices," Journal of The Electrochemical Society, 148 (5) G265-G270 (2001).
	49.	Girshick et al., "Numerical Modeling of Gas-Phase Nucleation and Particle Growth during Chemical Vapor Deposition of Silicon," Journal of The Electrochemical Society, 147 (6) 2303-2311 (2000).
	50.	Fonzo, et al., "Focused nanoparticle-beam deposition of patterned microstructures," Applied Physics Letters, Volume 77, Number 6, August 7, 2000, pages 910-912.
	51.	Notice of Allowance mailed May 22, 2006, from U.S. Application No. 10/672,311 [Atty Dkt No. NOVLP075/NVLS-2820].
	52.	Allowed Claims from U.S. Application No. 10/672,311 [Atty Dkt No. NOVLP075/NVLS-2820]
	53.	Notice of Allowance mailed October 3, 2006, from U.S. Application No. 10/785,235 [Atty Dkt No. NOVLP085/NVLS-2875].
	54.	Allowed Claims from U.S. Application No. 10/785,235 [Atty Dkt No. NOVLP085/NVLS-2875]

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	55.	U.S. Office Action mailed December 12, 2007, from U.S Application No. 11/146,456 [Atty Dkt No. NOVLP100X1/NVLS-3040].
	56.	Qingguo W and Karne K. Gleason, "Pulsed Plasma CVD of OSG and OSG/Organic Copolymer Films", June 2002.
	57.	Richard J. Lewis, Sr, Hawley's 'Condensed Chemical Dictionary, 12 <sup>th</sup> Edition, Copyright 1993, pp. 917-918 and 1124

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